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Eighth Semester B.Tech. Degree Examination, May 2013 (2008 Scheme) 08.801: NANOELECTRONICS (TA)

Time: 3 Hours

PART - A

Answer all questions. Each question carries 4 marks.

- 1. Write notes on precipitation of quantum dots.
- 2. Briefly explain the laser ablation method for nano material deposition.
- 3. Explain the principle of operation of an STM.
- 4. Show that the density of states in a one dimensional semiconductor material is directly proportional to $\frac{1}{\sqrt{E}}$.
- 5. With the help of energy band diagram, explain the two types of multiple quantum wells.
- 6. Consider an electron having kinetic energy 5 eV and rest mass 0.511 MeV. Calculate its de Broglie wavelength.
- 7. List the benefits of carbon nanotube FETs. manpails vone and one and
- 8. Explain quantum confined stark effect with reference to quantum well optical modulator.
- Draw the schematic representation of the conduction band of a resonant tunnel diode for
 - a) no voltage applied
 - b) increasing applied voltageExplain its IV characteristics.
- Explain the Aharonov-Bohm quantum interference effects.





PART-B

Answer any two questions from each module. Each question carries 10 marks.

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- 11. Explain the sol-gel process for fabrication of nano particles.
- 12. Explain the principle of operation of an AFM.
 - 13. Draw and label a CVD reactor and explain the steps involved in CVD processes.

MODULE – II

- 14. Explain the concept of quantization of conductance and coulomb blockade with reference to quantum transport in nano structures.
- 15. Explain the Shubnikov-de Hass effect of magnetic fields on the electronic and transport properties of the 2D system.
- 16. Determine the electron wavefunction for a finite potential square well. State all the assumptions clearly.

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- 17. Explain coulomb blockade effect and the working of a single electron transistor.
- 18. The heterojunction bipolar transistor is an improvement of the BJT. Justify.
- With the aid of energy diagram, explain the working of a resonant tunneling transistor.